Renesas Electronics America Inc - R5F100MFDFA#X0 Datasheet

Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I²C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	64
Program Memory Size	96KB (96K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 17x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	80-LQFP
Supplier Device Package	80-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f100mfdfa-x0

Table 1-1. List of Ordering Part Numbers

(7/12)

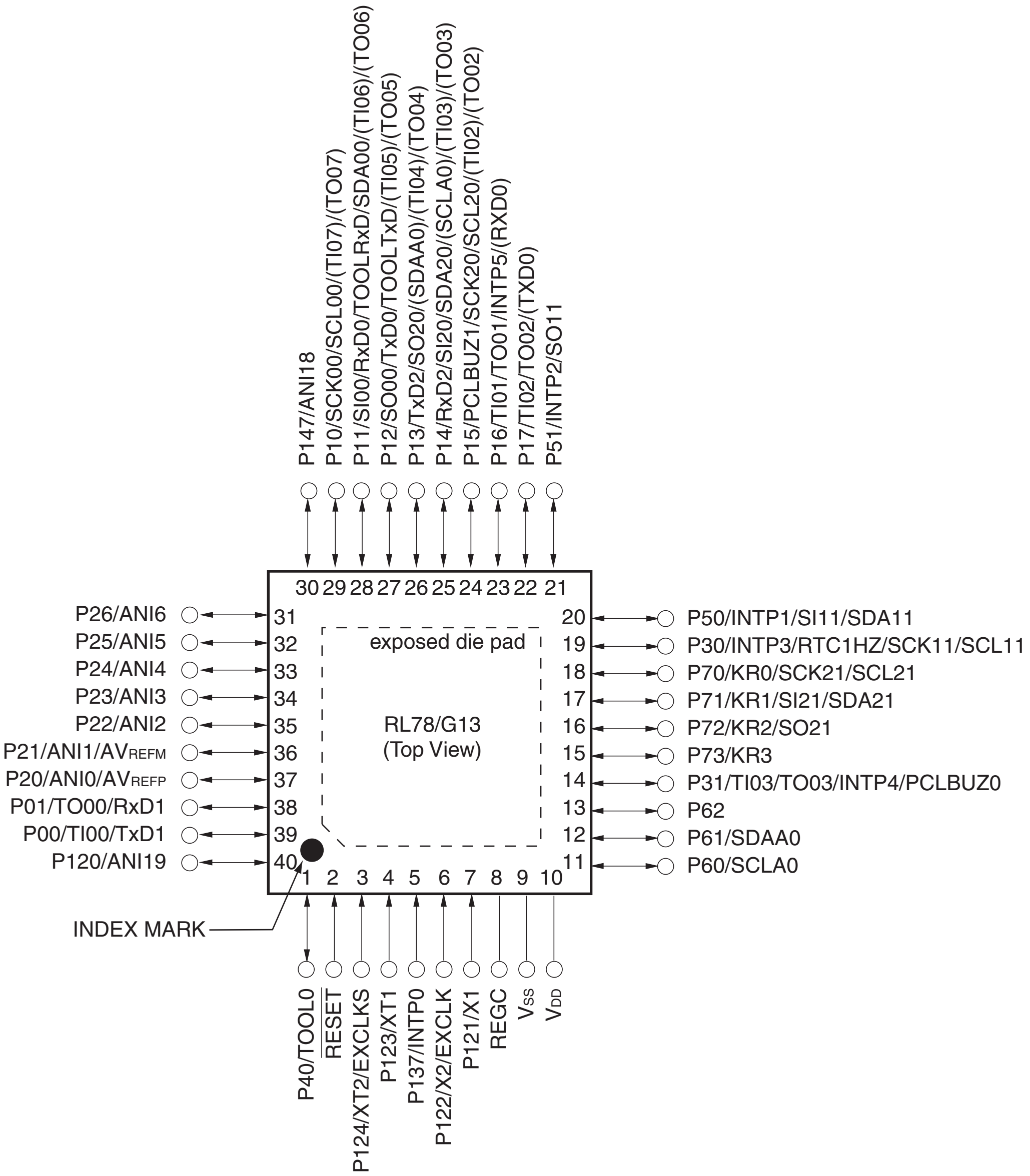
Pin count	Package	Data flash	Fields of Application Note	Ordering Part Number
52 pins	52-pin plastic LQFP (10 × 10 mm, 0.65 mm pitch)	Mounted	A	R5F100JCAFA#V0, R5F100JDAFA#V0, R5F100JEAFA#V0, R5F100JFAFA#V0, R5F100JGAFA#V0, R5F100JHAFA#V0, R5F100JJAFA#V0, R5F100JKAFA#V0, R5F100JLAFA#V0 R5F100JCAFA#X0, R5F100JDAFA#X0, R5F100JEAFA#X0, R5F100JFAFA#X0, R5F100JGAFA#X0, R5F100JHAFA#X0, R5F100JJAFA#X0, R5F100JKAFA#X0, R5F100JLAFA#X0
			D	R5F100JCDFA#V0, R5F100JDDFA#V0, R5F100JEDFA#V0, R5F100JFDFA#V0, R5F100JGDFA#V0, R5F100JHDFA#V0, R5F100JJDFA#V0, R5F100JKDFA#V0, R5F100JLDFA#V0 R5F100JCDFA#X0, R5F100JDDFA#X0, R5F100JEDFA#X0, R5F100JFDFA#X0, R5F100JGDFA#X0, R5F100JHDFA#X0, R5F100JJDFA#X0, R5F100JKDFA#X0, R5F100JLDFA#X0
			G	R5F100JCGFA#V0, R5F100JDGFA#V0, R5F100JEGFA#V0, R5F100JFGFA#V0,R5F100JGGFA#V0, R5F100JHGFA#V0, R5F100JJGFA#V0 R5F100JCGFA#X0, R5F100JDGFA#X0, R5F100JEGFA#X0, R5F100JFGFA#X0,R5F100JGGFA#X0, R5F100JHGFA#X0, R5F100JJGFA#X0
		Not mounted	A	R5F101JCAFA#V0, R5F101JDAFA#V0, R5F101JEAFA#V0, R5F101JFAFA#V0, R5F101JGAFA#V0, R5F101JHAFA#V0, R5F101JJAFA#V0, R5F101JKAFA#V0, R5F101JLAFA#V0 R5F101JCAFA#X0, R5F101JDAFA#X0, R5F101JEAFA#X0, R5F101JFAFA#X0, R5F101JGAFA#X0, R5F101JHAFA#X0, R5F101JJAFA#X0, R5F101JKAFA#X0, R5F101JLAFA#X0
			D	R5F101JCDFA#V0, R5F101JDDFA#V0, R5F101JEDFA#V0, R5F101JFDFA#V0, R5F101JGDFA#V0, R5F101JHDFA#V0, R5F101JJDFA#V0, R5F101JKDFA#V0, R5F101JLDFA#V0 R5F101JCDFA#X0, R5F101JDDFA#X0, R5F101JEDFA#X0, R5F101JFDFA#X0, R5F101JGDFA#X0, R5F101JHDFA#X0, R5F101JJDFA#X0, R5F101JKDFA#X0, R5F101JLDFA#X0

Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.3.7 40-pin products

- 40-pin plastic HWQFN (6 × 6 mm, 0.5 mm pitch)



Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μF).

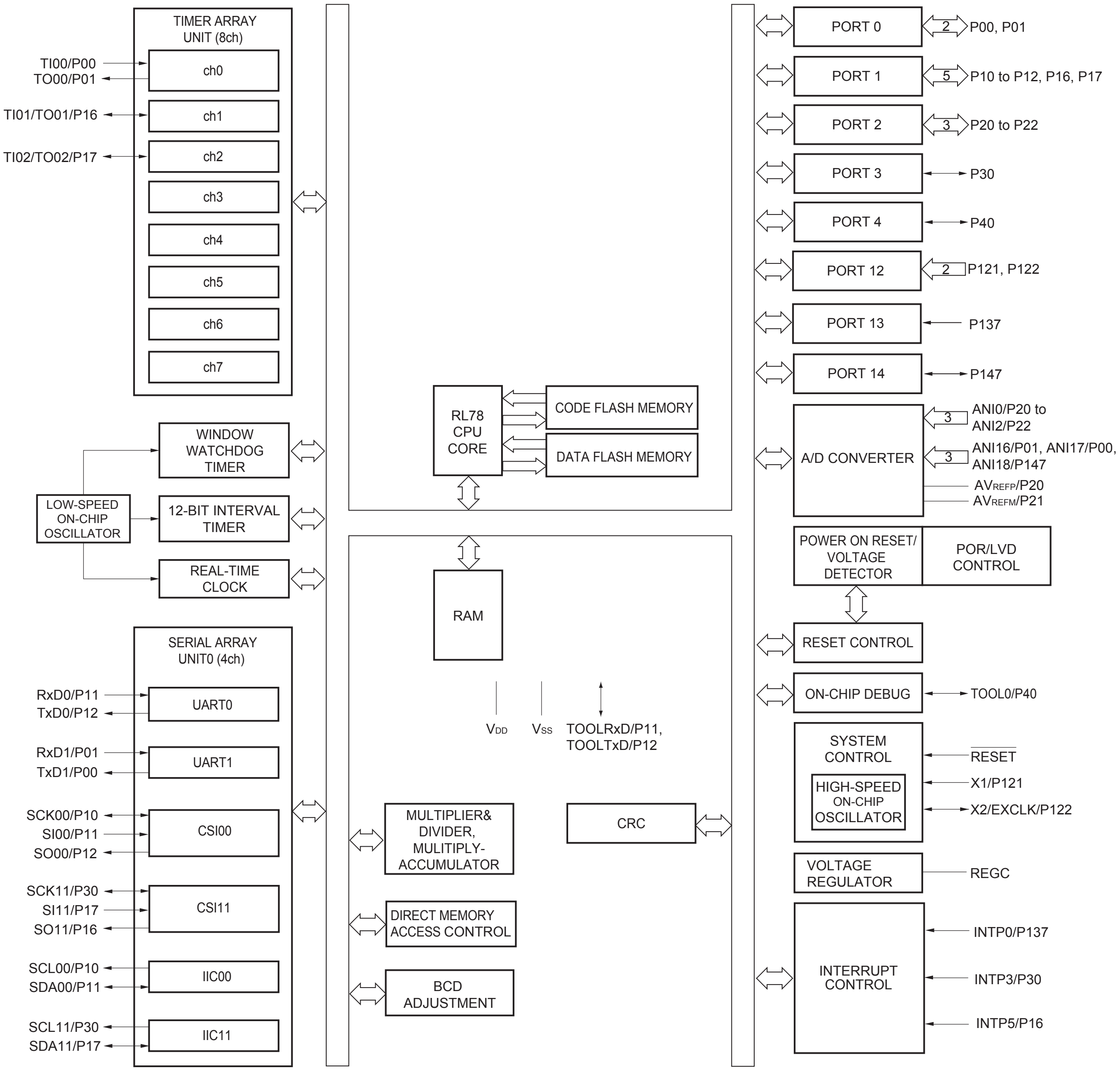
Remarks 1. For pin identification, see **1.4 Pin Identification**.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

3. It is recommended to connect an exposed die pad to V_{SS}.

1.5 Block Diagram

1.5.1 20-pin products



1.6 Outline of Functions

[20-pin, 24-pin, 25-pin, 30-pin, 32-pin, 36-pin products]

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

(1/2)

Item		20-pin		24-pin		25-pin		30-pin		32-pin		36-pin	
		R5F1006x	R5F1016x	R5F1007x	R5F1017x	R5F1008x	R5F1018x	R5F100Ax	R5F101Ax	R5F100Bx	R5F101Bx	R5F100Cx	R5F101Cx
Code flash memory (KB)		16 to 64		16 to 64		16 to 64		16 to 128		16 to 128		16 to 128	
Data flash memory (KB)		4	–	4	–	4	–	4 to 8	–	4 to 8	–	4 to 8	–
RAM (KB)		2 to 4 Note1		2 to 4 Note1		2 to 4 Note1		2 to 12 Note1		2 to 12 Note1		2 to 12 Note1	
Address space		1 MB											
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (High-speed main) mode: 1 to 20 MHz (V_{DD} = 2.7 to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz (V_{DD} = 2.4 to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz (V_{DD} = 1.8 to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz (V_{DD} = 1.6 to 5.5 V)											
	High-speed on-chip oscillator	HS (High-speed main) mode: 1 to 32 MHz (V_{DD} = 2.7 to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz (V_{DD} = 2.4 to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz (V_{DD} = 1.8 to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz (V_{DD} = 1.6 to 5.5 V)											
Subsystem clock		–											
Low-speed on-chip oscillator		15 kHz (TYP.)											
General-purpose registers		(8-bit register × 8) × 4 banks											
Minimum instruction execution time		0.03125 µs (High-speed on-chip oscillator: f_{IH} = 32 MHz operation)											
		0.05 µs (High-speed system clock: f_{MX} = 20 MHz operation)											
Instruction set		• Data transfer (8/16 bits) • Adder and subtractor/logical operation (8/16 bits) • Multiplication (8 bits × 8 bits) • Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc.											
I/O port	Total	16		20		21		26		28		32	
	CMOS I/O	13 (N-ch O.D. I/O [V_{DD} withstand voltage]: 5)		15 (N-ch O.D. I/O [V_{DD} withstand voltage]: 6)		15 (N-ch O.D. I/O [V_{DD} withstand voltage]: 6)		21 (N-ch O.D. I/O [V_{DD} withstand voltage]: 9)		22 (N-ch O.D. I/O [V_{DD} withstand voltage]: 9)		26 (N-ch O.D. I/O [V_{DD} withstand voltage]: 10)	
	CMOS input	3		3		3		3		3		3	
	CMOS output	–		–		1		–		–		–	
	N-ch O.D. I/O (withstand voltage: 6 V)	–		2		2		2		3		3	
Timer	16-bit timer	8 channels											
	Watchdog timer	1 channel											
	Real-time clock (RTC)	1 channel Note 2											
	12-bit interval timer (IT)	1 channel											
	Timer output	3 channels (PWM outputs: 2 Note 3)		4 channels (PWM outputs: 3 Note 3)				4 channels (PWM outputs: 3 Note 3), 8 channels (PWM outputs: 7 Note 3) Note 4					
	RTC output	–											

Notes 1. The flash library uses RAM in self-programming and rewriting of the data flash memory.
The target products and start address of the RAM areas used by the flash library are shown below.
R5F100xD, R5F101xD (x = 6 to 8, A to C): Start address FF300H
R5F100xE, R5F101xE (x = 6 to 8, A to C): Start address FEF00H
For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

2. Only the constant-period interrupt function when the low-speed on-chip oscillator clock (f_{IL}) is selected

(T_A = –40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (3/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	V_{IH1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	Normal input buffer	$0.8EV_{DD0}$		EV_{DD0}	V
	V_{IH2}	P01, P03, P04, P10, P11, P13 to P17, P43, P44, P53 to P55, P80, P81, P142, P143	TTL input buffer 4.0 V ≤ EV_{DD0} ≤ 5.5 V	2.2		EV_{DD0}	V
			TTL input buffer 3.3 V ≤ EV_{DD0} < 4.0 V	2.0		EV_{DD0}	V
			TTL input buffer 1.6 V ≤ EV_{DD0} < 3.3 V	1.5		EV_{DD0}	V
	V_{IH3}	P20 to P27, P150 to P156		$0.7V_{DD}$		V_{DD}	V
	V_{IH4}	P60 to P63		$0.7EV_{DD0}$		6.0	V
	V_{IH5}	P121 to P124, P137, EXCLK, EXCLKS, $\overline{\text{RESET}}$		$0.8V_{DD}$		V_{DD}	V
Input voltage, low	V_{IL1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	Normal input buffer	0		$0.2EV_{DD0}$	V
	V_{IL2}	P01, P03, P04, P10, P11, P13 to P17, P43, P44, P53 to P55, P80, P81, P142, P143	TTL input buffer 4.0 V ≤ EV_{DD0} ≤ 5.5 V	0		0.8	V
			TTL input buffer 3.3 V ≤ EV_{DD0} < 4.0 V	0		0.5	V
			TTL input buffer 1.6 V ≤ EV_{DD0} < 3.3 V	0		0.32	V
	V_{IL3}	P20 to P27, P150 to P156		0		$0.3V_{DD}$	V
	V_{IL4}	P60 to P63		0		$0.3EV_{DD0}$	V
	V_{IL5}	P121 to P124, P137, EXCLK, EXCLKS, $\overline{\text{RESET}}$		0		$0.2V_{DD}$	V

Caution The maximum value of V_{IH} of pins P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 is EV_{DD0}, even in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(4) Peripheral Functions (Common to all products)

(T_A = –40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Low-speed on-chip oscillator operating current	I_{FIL} Note 1				0.20		μA
RTC operating current	I_{RTC} Notes 1, 2, 3				0.02		μA
12-bit interval timer operating current	I_{IT} Notes 1, 2, 4				0.02		μA
Watchdog timer operating current	I_{WDT} Notes 1, 2, 5	f_{IL} = 15 kHz			0.22		μA
A/D converter operating current	I_{ADC} Notes 1, 6	When conversion at maximum speed	Normal mode, AV_{REFP} = V_{DD} = 5.0 V		1.3	1.7	mA
			Low voltage mode, AV_{REFP} = V_{DD} = 3.0 V		0.5	0.7	mA
A/D converter reference voltage current	I_{ADREF} Note 1				75.0		μA
Temperature sensor operating current	I_{TMPS} Note 1				75.0		μA
LVD operating current	I_{LVI} Notes 1, 7				0.08		μA
Self-programming operating current	I_{FSP} Notes 1, 9				2.50	12.20	mA
BGO operating current	I_{BGO} Notes 1, 8				2.50	12.20	mA
SNOOZE operating current	I_{SNOZ} Note 1	ADC operation	The mode is performed Note 10		0.50	0.60	mA
			The A/D conversion operations are performed, Low voltage mode, AV_{REFP} = V_{DD} = 3.0 V		1.20	1.44	mA
		CSI/UART operation			0.70	0.84	mA

Notes 1. Current flowing to V_{DD}.

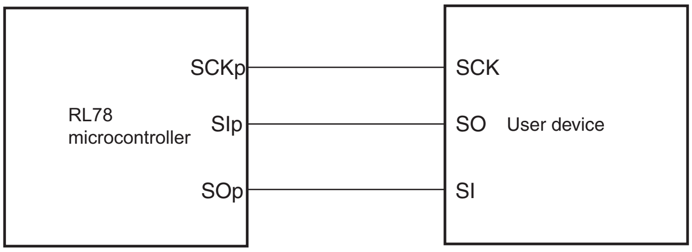
2. When high speed on-chip oscillator and high-speed system clock are stopped.

3. Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either I_{DD1} or I_{DD2}, and I_{RTC}, when the real-time clock operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, I_{FIL} should be added. I_{DD2} subsystem clock operation includes the operational current of the real-time clock.

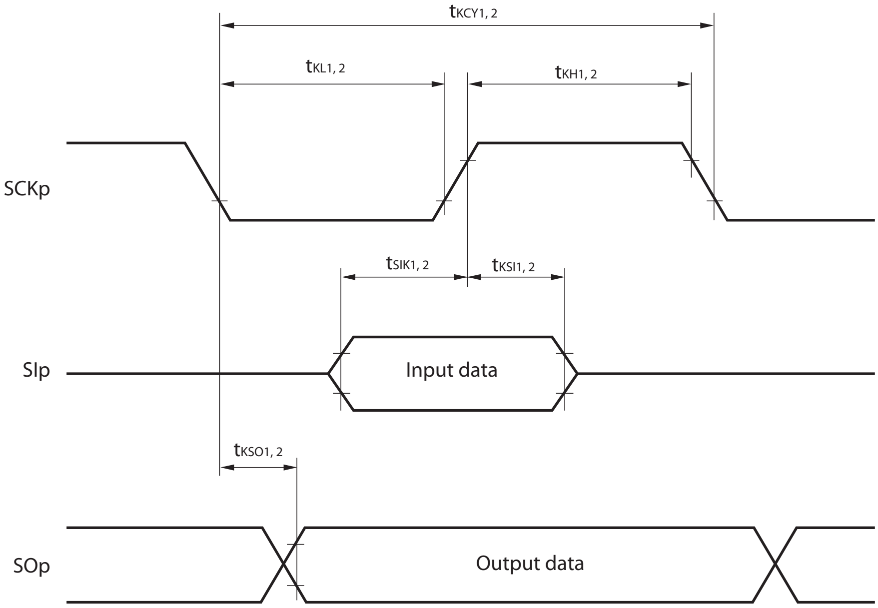
4. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either I_{DD1} or I_{DD2}, and I_{IT}, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, I_{FIL} should be added.

5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The supply current of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3} and I_{WDT} when the watchdog timer is in operation.

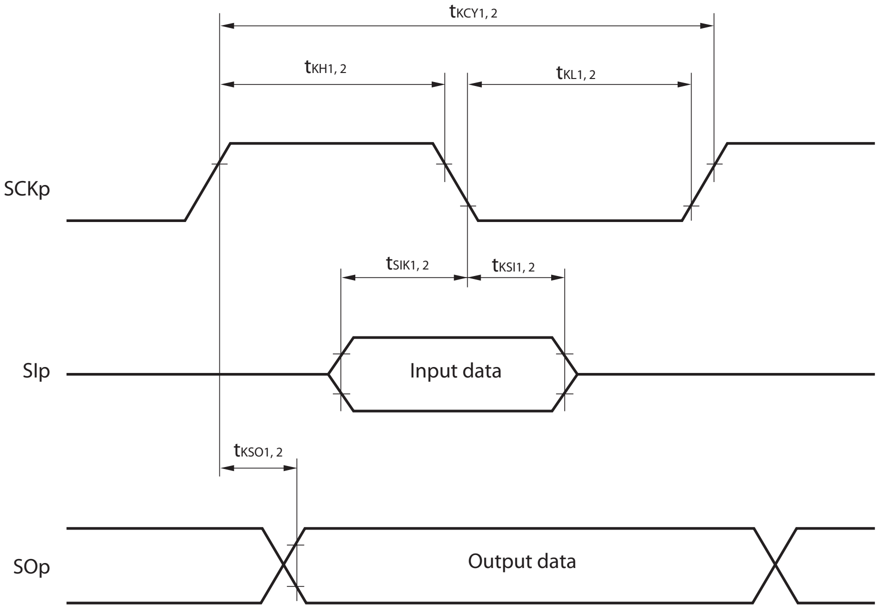
CSI mode connection diagram (during communication at same potential)



CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31)

2. m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (3/3)

($T_A = -40$ to $+85°C$, $1.8\ V \le EV_{DD0} = EV_{DD1} \le V_{DD} \le 5.5\ V$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0\ V$)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↓) Note 1	t_{SIK1}	$4.0\ V \le EV_{DD0} \le 5.5\ V$, $2.7\ V \le V_b \le 4.0\ V$, $C_b = 30\ pF$, $R_b = 1.4\ k\Omega$	44		110		110		ns
		$2.7\ V \le EV_{DD0} < 4.0\ V$, $2.3\ V \le V_b \le 2.7\ V$, $C_b = 30\ pF$, $R_b = 2.7\ k\Omega$	44		110		110		ns
		$1.8\ V \le EV_{DD0} < 3.3\ V$, $1.6\ V \le V_b \le 2.0\ V$ Note 2, $C_b = 30\ pF$, $R_b = 5.5\ k\Omega$	110		110		110		ns
SIp hold time (from SCKp↓) Note 1	t_{KSI1}	$4.0\ V \le EV_{DD0} \le 5.5\ V$, $2.7\ V \le V_b \le 4.0\ V$, $C_b = 30\ pF$, $R_b = 1.4\ k\Omega$	19		19		19		ns
		$2.7\ V \le EV_{DD0} < 4.0\ V$, $2.3\ V \le V_b \le 2.7\ V$, $C_b = 30\ pF$, $R_b = 2.7\ k\Omega$	19		19		19		ns
		$1.8\ V \le EV_{DD0} < 3.3\ V$, $1.6\ V \le V_b \le 2.0\ V$ Note 2, $C_b = 30\ pF$, $R_b = 5.5\ k\Omega$	19		19		19		ns
Delay time from SCKp↑ to SOp output Note 1	t_{KSO1}	$4.0\ V \le EV_{DD0} \le 5.5\ V$, $2.7\ V \le V_b \le 4.0\ V$, $C_b = 30\ pF$, $R_b = 1.4\ k\Omega$		25		25		25	ns
		$2.7\ V \le EV_{DD0} < 4.0\ V$, $2.3\ V \le V_b \le 2.7\ V$, $C_b = 30\ pF$, $R_b = 2.7\ k\Omega$		25		25		25	ns
		$1.8\ V \le EV_{DD0} < 3.3\ V$, $1.6\ V \le V_b \le 2.0\ V$ Note 2, $C_b = 30\ pF$, $R_b = 5.5\ k\Omega$		25		25		25	ns

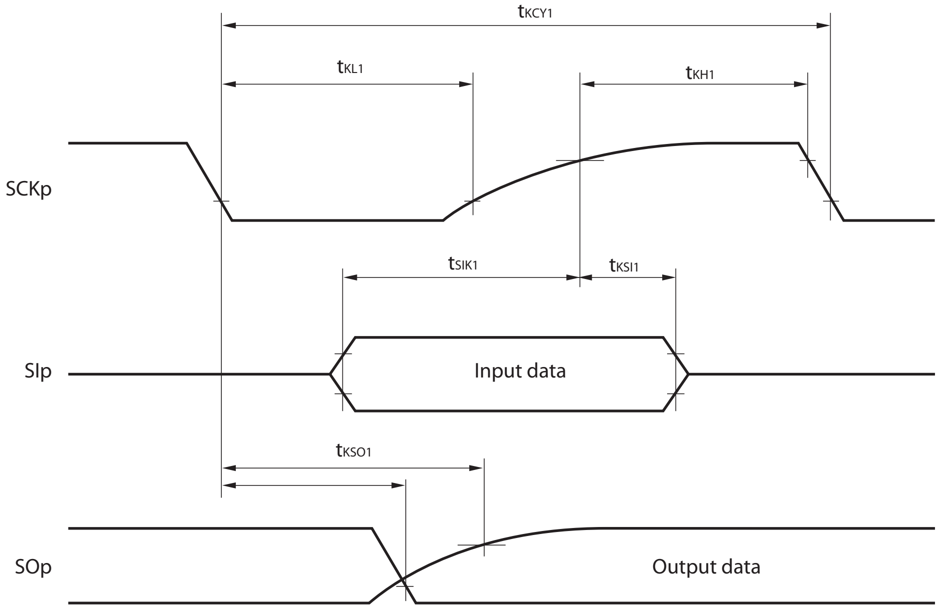
Notes **1.** When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

2. Use it with $EV_{DD0} \ge V_b$.

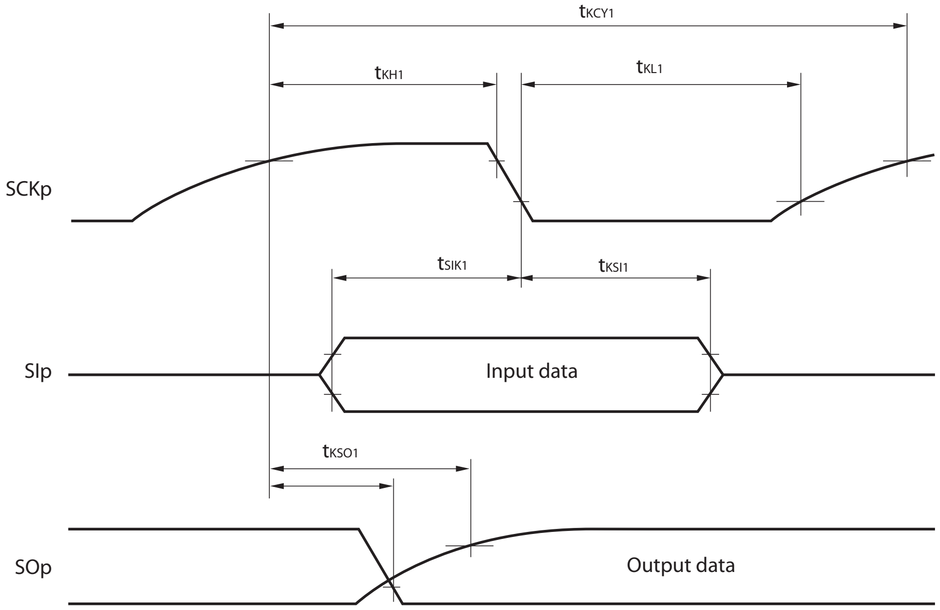
Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance (When 20- to 52-pin products)/EV_{DD} tolerance (When 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(**Remarks** are listed on the next page.)

CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)

2. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

(9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

(T_A = −40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (2/2)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp high-/low-level width	t_{KH2}, t_{KL2}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V	$t_{KCY2}/2 - 12$		$t_{KCY2}/2 - 50$		$t_{KCY2}/2 - 50$		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V	$t_{KCY2}/2 - 18$		$t_{KCY2}/2 - 50$		$t_{KCY2}/2 - 50$		ns
		1.8 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2	$t_{KCY2}/2 - 50$		$t_{KCY2}/2 - 50$		$t_{KCY2}/2 - 50$		ns
SIp setup time (to SCKp↑) Note 3	t_{SIK2}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V	$1/f_{MCK} + 20$		$1/f_{MCK} + 30$		$1/f_{MCK} + 30$		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V	$1/f_{MCK} + 20$		$1/f_{MCK} + 30$		$1/f_{MCK} + 30$		ns
		1.8 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2	$1/f_{MCK} + 30$		$1/f_{MCK} + 30$		$1/f_{MCK} + 30$		ns
SIp hold time (from SCKp↑) Note 4	t_{KSI2}		$1/f_{MCK} + 31$		$1/f_{MCK} + 31$		$1/f_{MCK} + 31$		ns
Delay time from SCKp↓ to SOp output Note 5	t_{KSO2}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		$2/f_{MCK} + 120$		$2/f_{MCK} + 573$		$2/f_{MCK} + 573$	ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		$2/f_{MCK} + 214$		$2/f_{MCK} + 573$		$2/f_{MCK} + 573$	ns
		1.8 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 30 pF, R_b = 5.5 kΩ		$2/f_{MCK} + 573$		$2/f_{MCK} + 573$		$2/f_{MCK} + 573$	ns

Notes 1. Transfer rate in the SNOOZE mode : MAX. 1 Mbps

2. Use it with EV_{DD0} ≥ V_b.

3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

5. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(**Remarks** are listed on the next page.)

2.5.2 Serial interface IICA

(1) I^2C standard mode

(T_A = –40 to +85°C, $1.6\ V \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5\ V$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0\ V$)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	f_{SCL}	Standard mode: $f_{CLK} \geq 1$ MHz	$2.7\ V \leq EV_{DD0} \leq 5.5\ V$	0	100	0	100	0	100	kHz
			$1.8\ V \leq EV_{DD0} \leq 5.5\ V$	0	100	0	100	0	100	kHz
			$1.7\ V \leq EV_{DD0} \leq 5.5\ V$	0	100	0	100	0	100	kHz
			$1.6\ V \leq EV_{DD0} \leq 5.5\ V$	—		0	100	0	100	kHz
Setup time of restart condition	$t_{SU:STA}$	$2.7\ V \leq EV_{DD0} \leq 5.5\ V$		4.7		4.7		4.7		μs
		$1.8\ V \leq EV_{DD0} \leq 5.5\ V$		4.7		4.7		4.7		μs
		$1.7\ V \leq EV_{DD0} \leq 5.5\ V$		4.7		4.7		4.7		μs
		$1.6\ V \leq EV_{DD0} \leq 5.5\ V$		—		4.7		4.7		μs
Hold time[Note 1]	$t_{HD:STA}$	$2.7\ V \leq EV_{DD0} \leq 5.5\ V$		4.0		4.0		4.0		μs
		$1.8\ V \leq EV_{DD0} \leq 5.5\ V$		4.0		4.0		4.0		μs
		$1.7\ V \leq EV_{DD0} \leq 5.5\ V$		4.0		4.0		4.0		μs
		$1.6\ V \leq EV_{DD0} \leq 5.5\ V$		—		4.0		4.0		μs
Hold time when SCLA0 = "L"	t_{LOW}	$2.7\ V \leq EV_{DD0} \leq 5.5\ V$		4.7		4.7		4.7		μs
		$1.8\ V \leq EV_{DD0} \leq 5.5\ V$		4.7		4.7		4.7		μs
		$1.7\ V \leq EV_{DD0} \leq 5.5\ V$		4.7		4.7		4.7		μs
		$1.6\ V \leq EV_{DD0} \leq 5.5\ V$		—		4.7		4.7		μs
Hold time when SCLA0 = "H"	t_{HIGH}	$2.7\ V \leq EV_{DD0} \leq 5.5\ V$		4.0		4.0		4.0		μs
		$1.8\ V \leq EV_{DD0} \leq 5.5\ V$		4.0		4.0		4.0		μs
		$1.7\ V \leq EV_{DD0} \leq 5.5\ V$		4.0		4.0		4.0		μs
		$1.6\ V \leq EV_{DD0} \leq 5.5\ V$		—		4.0		4.0		μs
Data setup time (reception)	$t_{SU:DAT}$	$2.7\ V \leq EV_{DD0} \leq 5.5\ V$		250		250		250		ns
		$1.8\ V \leq EV_{DD0} \leq 5.5\ V$		250		250		250		ns
		$1.7\ V \leq EV_{DD0} \leq 5.5\ V$		250		250		250		ns
		$1.6\ V \leq EV_{DD0} \leq 5.5\ V$		—		250		250		ns
Data hold time (transmission)[Note 2]	$t_{HD:DAT}$	$2.7\ V \leq EV_{DD0} \leq 5.5\ V$		0	3.45	0	3.45	0	3.45	μs
		$1.8\ V \leq EV_{DD0} \leq 5.5\ V$		0	3.45	0	3.45	0	3.45	μs
		$1.7\ V \leq EV_{DD0} \leq 5.5\ V$		0	3.45	0	3.45	0	3.45	μs
		$1.6\ V \leq EV_{DD0} \leq 5.5\ V$		—		0	3.45	0	3.45	μs
Setup time of stop condition	$t_{SU:STO}$	$2.7\ V \leq EV_{DD0} \leq 5.5\ V$		4.0		4.0		4.0		μs
		$1.8\ V \leq EV_{DD0} \leq 5.5\ V$		4.0		4.0		4.0		μs
		$1.7\ V \leq EV_{DD0} \leq 5.5\ V$		4.0		4.0		4.0		μs
		$1.6\ V \leq EV_{DD0} \leq 5.5\ V$		—		4.0		4.0		μs
Bus-free time	t_{BUF}	$2.7\ V \leq EV_{DD0} \leq 5.5\ V$		4.7		4.7		4.7		μs
		$1.8\ V \leq EV_{DD0} \leq 5.5\ V$		4.7		4.7		4.7		μs
		$1.7\ V \leq EV_{DD0} \leq 5.5\ V$		4.7		4.7		4.7		μs
		$1.6\ V \leq EV_{DD0} \leq 5.5\ V$		—		4.7		4.7		μs

(**Notes**, **Caution** and **Remark** are listed on the next page.)

2.6 Analog Characteristics

2.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Input channel	Reference Voltage		
	Reference voltage (+) = AV_{REFP} Reference voltage (–) = AV_{REFM}	Reference voltage (+) = V_{DD} Reference voltage (–) = V_{SS}	Reference voltage (+) = V_{BGR} Reference voltage (–) = AV_{REFM}
ANI0 to ANI14	Refer to **2.6.1 (1)**.	Refer to **2.6.1 (3)**.	Refer to **2.6.1 (4)**.
ANI16 to ANI26	Refer to **2.6.1 (2)**.		
Internal reference voltage Temperature sensor output voltage	Refer to **2.6.1 (1)**.		–

(1) When reference voltage (+)= AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (–) = AV_{REFM}/ANI1 (ADREFM = 1), target pin : ANI2 to ANI14, internal reference voltage, and temperature sensor output voltage

(T_A = –40 to +85°C, $1.6\ V \le AV_{REFP} \le V_{DD} \le 5.5\ V$, $V_{SS} = 0\ V$, Reference voltage (+) = AV_{REFP}, Reference voltage (–) = $AV_{REFM} = 0\ V$)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error[Note 1]	AINL	10-bit resolution $AV_{REFP} = V_{DD}$ [Note 3]	$1.8\ V \le AV_{REFP} \le 5.5\ V$		1.2	±3.5	LSB
			$1.6\ V \le AV_{REFP} \le 5.5\ V$ [Note 4]		1.2	±7.0	LSB
Conversion time	t_{CONV}	10-bit resolution Target pin: ANI2 to ANI14	$3.6\ V \le V_{DD} \le 5.5\ V$	2.125		39	μs
			$2.7\ V \le V_{DD} \le 5.5\ V$	3.1875		39	μs
			$1.8\ V \le V_{DD} \le 5.5\ V$	17		39	μs
			$1.6\ V \le V_{DD} \le 5.5\ V$	57		95	μs
		10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$3.6\ V \le V_{DD} \le 5.5\ V$	2.375		39	μs
			$2.7\ V \le V_{DD} \le 5.5\ V$	3.5625		39	μs
			$2.4\ V \le V_{DD} \le 5.5\ V$	17		39	μs
Zero-scale error[Notes 1, 2]	E_{ZS}	10-bit resolution $AV_{REFP} = V_{DD}$ [Note 3]	$1.8\ V \le AV_{REFP} \le 5.5\ V$			±0.25	%FSR
			$1.6\ V \le AV_{REFP} \le 5.5\ V$ [Note 4]			±0.50	%FSR
Full-scale error[Notes 1, 2]	E_{FS}	10-bit resolution $AV_{REFP} = V_{DD}$ [Note 3]	$1.8\ V \le AV_{REFP} \le 5.5\ V$			±0.25	%FSR
			$1.6\ V \le AVREFP \le 5.5\ V$ [Note 4]			±0.50	%FSR
Integral linearity error[Note 1]	ILE	10-bit resolution $AV_{REFP} = V_{DD}$ [Note 3]	$1.8\ V \le AV_{REFP} \le 5.5\ V$			±2.5	LSB
			$1.6\ V \le AV_{REFP} \le 5.5\ V$ [Note 4]			±5.0	LSB
Differential linearity error[Note 1]	DLE	10-bit resolution $AV_{REFP} = V_{DD}$ [Note 3]	$1.8\ V \le AV_{REFP} \le 5.5\ V$			±1.5	LSB
			$1.6\ V \le AV_{REFP} \le 5.5\ V$ [Note 4]			±2.0	LSB
Analog input voltage	V_{AIN}	ANI2 to ANI14		0		AV_{REFP}	V
		Internal reference voltage ($2.4\ V \le V_{DD} \le 5.5\ V$, HS (high-speed main) mode)		V_{BGR} [Note 5]			V
		Temperature sensor output voltage ($2.4\ V \le V_{DD} \le 5.5\ V$, HS (high-speed main) mode)		V_{TMPS25} [Note 5]			V

(**Notes** are listed on the next page.)

(2) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (–) = AV_{REFM}/ANI1 (ADREFM = 1), target pin : ANI16 to ANI26

(T_A = –40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, 1.6 V ≤ AV_{REFP} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V, Reference voltage (+) = AV_{REFP}, Reference voltage (–) = AV_{REFM} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error[Note 1]	AINL	10-bit resolution EV_{DD0} = AV_{REFP} = V_{DD} [Notes 3, 4]	1.8 V ≤ AV_{REFP} ≤ 5.5 V		1.2	±5.0	LSB
			1.6 V ≤ AV_{REFP} ≤ 5.5 V [Note 5]		1.2	±8.5	LSB
Conversion time	t_{CONV}	10-bit resolution Target ANI pin : ANI16 to ANI26	3.6 V ≤ V_{DD} ≤ 5.5 V	2.125		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.1875		39	μs
			1.8 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
			1.6 V ≤ V_{DD} ≤ 5.5 V	57		95	μs
Zero-scale error[Notes 1, 2]	E_{ZS}	10-bit resolution EV_{DD0} = AV_{REFP} = V_{DD} [Notes 3, 4]	1.8 V ≤ AV_{REFP} ≤ 5.5 V			±0.35	%FSR
			1.6 V ≤ AV_{REFP} ≤ 5.5 V [Note 5]			±0.60	%FSR
Full-scale error[Notes 1, 2]	E_{FS}	10-bit resolution EV_{DD0} = AV_{REFP} = V_{DD} [Notes 3, 4]	1.8 V ≤ AV_{REFP} ≤ 5.5 V			±0.35	%FSR
			1.6 V ≤ AV_{REFP} ≤ 5.5 V [Note 5]			±0.60	%FSR
Integral linearity error[Note 1]	ILE	10-bit resolution EV_{DD0} = AV_{REFP} = V_{DD} [Notes 3, 4]	1.8 V ≤ AV_{REFP} ≤ 5.5 V			±3.5	LSB
			1.6 V ≤ AV_{REFP} ≤ 5.5 V [Note 5]			±6.0	LSB
Differential linearity error[Note 1]	DLE	10-bit resolution EV_{DD0} = AV_{REFP} = V_{DD} [Notes 3, 4]	1.8 V ≤ AV_{REFP} ≤ 5.5 V			±2.0	LSB
			1.6 V ≤ AV_{REFP} ≤ 5.5 V [Note 5]			±2.5	LSB
Analog input voltage	V_{AIN}	ANI16 to ANI26		0		AV_{REFP} and EV_{DD0}	V

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. When AV_{REFP} < V_{DD}, the MAX. values are as follows.
Overall error: Add ±1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.
Zero-scale error/Full-scale error: Add ±0.05%FSR to the MAX. value when AV_{REFP} = V_{DD}.
Integral linearity error/ Differential linearity error: Add ±0.5 LSB to the MAX. value when AV_{REFP} = V_{DD}.

4. When AV_{REFP} < EV_{DD0} ≤ V_{DD}, the MAX. values are as follows.
Overall error: Add ±4.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.
Zero-scale error/Full-scale error: Add ±0.20%FSR to the MAX. value when AV_{REFP} = V_{DD}.
Integral linearity error/ Differential linearity error: Add ±2.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

5. When the conversion time is set to 57 μs (min.) and 95 μs (max.).

(3) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (–) = V_{SS} (ADREFM = 0), target pin : ANI0 to ANI14, ANI16 to ANI26, internal reference voltage, and temperature sensor output voltage

(T_A = –40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V, Reference voltage (+) = V_{DD}, Reference voltage (–) = V_{SS})

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error[Note 1]	AINL	10-bit resolution	1.8 V ≤ V_{DD} ≤ 5.5 V		1.2	±7.0	LSB
			1.6 V ≤ V_{DD} ≤ 5.5 V[Note 3]		1.2	±10.5	LSB
Conversion time	t_{CONV}	10-bit resolution Target pin: ANI0 to ANI14, ANI16 to ANI26	3.6 V ≤ V_{DD} ≤ 5.5 V	2.125		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.1875		39	μs
			1.8 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
			1.6 V ≤ V_{DD} ≤ 5.5 V	57		95	μs
Conversion time	t_{CONV}	10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	3.6 V ≤ V_{DD} ≤ 5.5 V	2.375		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.5625		39	μs
			2.4 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
Zero-scale error[Notes 1, 2]	E_{ZS}	10-bit resolution	1.8 V ≤ V_{DD} ≤ 5.5 V			±0.60	%FSR
			1.6 V ≤ V_{DD} ≤ 5.5 V[Note 3]			±0.85	%FSR
Full-scale error[Notes 1, 2]	E_{FS}	10-bit resolution	1.8 V ≤ V_{DD} ≤ 5.5 V			±0.60	%FSR
			1.6 V ≤ V_{DD} ≤ 5.5 V[Note 3]			±0.85	%FSR
Integral linearity error[Note 1]	ILE	10-bit resolution	1.8 V ≤ V_{DD} ≤ 5.5 V			±4.0	LSB
			1.6 V ≤ V_{DD} ≤ 5.5 V[Note 3]			±6.5	LSB
Differential linearity error[Note 1]	DLE	10-bit resolution	1.8 V ≤ V_{DD} ≤ 5.5 V			±2.0	LSB
			1.6 V ≤ V_{DD} ≤ 5.5 V[Note 3]			±2.5	LSB
Analog input voltage	V_{AIN}	ANI0 to ANI14		0		V_{DD}	V
		ANI16 to ANI26		0		EV_{DD0}	V
		Internal reference voltage (2.4 V ≤ V_{DD} ≤ 5.5 V, HS (high-speed main) mode)			V_{BGR}[Note 4]		V
		Temperature sensor output voltage (2.4 V ≤ V_{DD} ≤ 5.5 V, HS (high-speed main) mode)			V_{TMPS25}[Note 4]		V

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

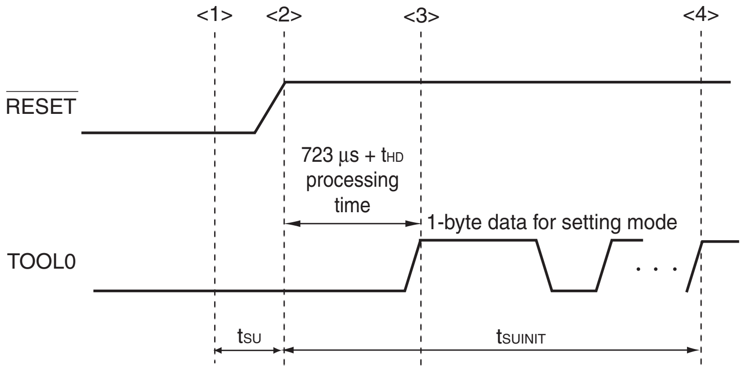
3. When the conversion time is set to 57 μs (min.) and 95 μs (max.).

4. Refer to **2.6.2 Temperature sensor/internal reference voltage characteristics**.

2.10 Timing of Entry to Flash Memory Programming Modes

(T_A = −40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	t_{SUINIT}	POR and LVD reset must be released before the external reset is released.			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	t_{SU}	POR and LVD reset must be released before the external reset is released.	10			μs
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)	t_{HD}	POR and LVD reset must be released before the external reset is released.	1			ms



<1> The low level is input to the TOOL0 pin.

<2> The external reset is released (POR and LVD reset must be released before the external reset is released.).

<3> The TOOL0 pin is set to the high level.

<4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark t_{SUINIT}: Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.

t_{SU}: Time to release the external reset after the TOOL0 pin is set to the low level

t_{HD}: Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)

(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)

(T_A = –40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions			HS (high-speed main) Mode		Unit
					MIN.	MAX.	
Transfer rate		Transmission	$4.0\ V \le EV_{DD0} \le 5.5\ V$, $2.7\ V \le V_b \le 4.0\ V$			**Note 1**	bps
				Theoretical value of the maximum transfer rate $C_b = 50\ pF$, $R_b = 1.4\ k\Omega$, $V_b = 2.7\ V$		2.6 Note 2	Mbps
			$2.7\ V \le EV_{DD0} < 4.0\ V$, $2.3\ V \le V_b \le 2.7\ V$			**Note 3**	bps
				Theoretical value of the maximum transfer rate $C_b = 50\ pF$, $R_b = 2.7\ k\Omega$, $V_b = 2.3\ V$		1.2 Note 4	Mbps
			$2.4\ V \le EV_{DD0} < 3.3\ V$, $1.6\ V \le V_b \le 2.0\ V$			**Note 5**	bps
				Theoretical value of the maximum transfer rate $C_b = 50\ pF$, $R_b = 5.5\ k\Omega$, $V_b = 1.6\ V$		0.43 Note 6	Mbps

Notes 1. The smaller maximum transfer rate derived by using $f_{MCK}/12$ or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when $4.0\ V \le EV_{DD0} \le 5.5\ V$ and $2.7\ V \le V_b \le 4.0\ V$

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\} \times 3}\ [\text{bps}]$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100\ [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

2. This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.

3. The smaller maximum transfer rate derived by using $f_{MCK}/12$ or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when $2.7\ V \le EV_{DD0} < 4.0\ V$ and $2.4\ V \le V_b \le 2.7\ V$

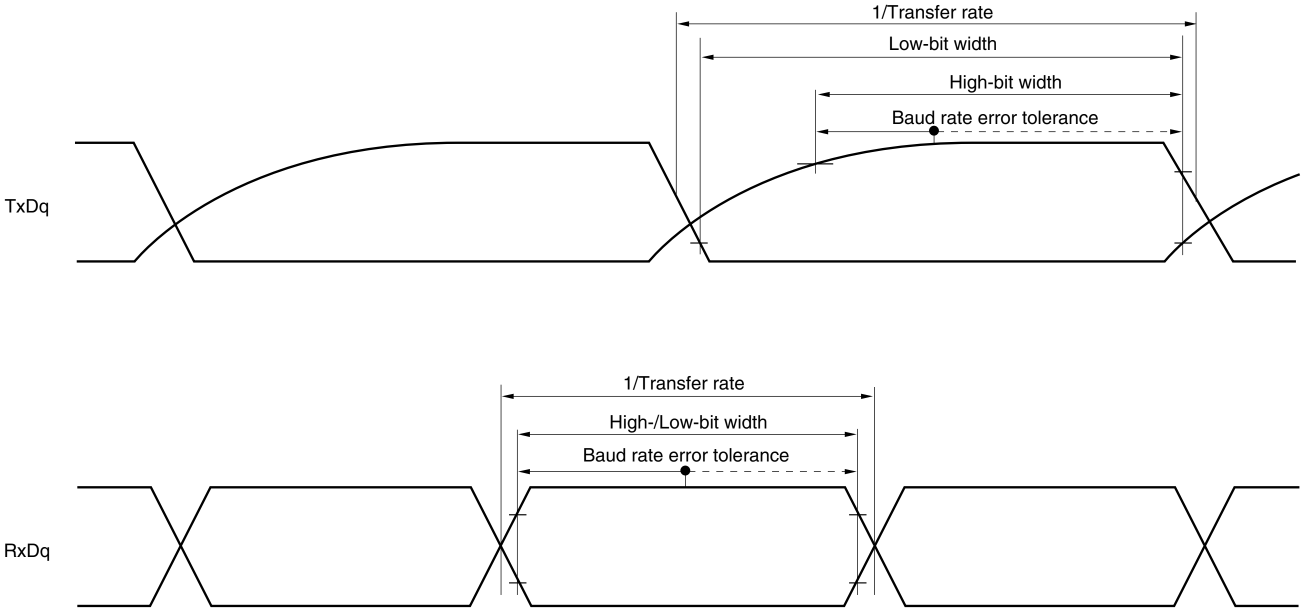
$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\} \times 3}\ [\text{bps}]$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100\ [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

4. This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.

UART mode bit width (during communication at different potential) (reference)



Remarks 1. R_b[Ω]:Communication line (TxDq) pull-up resistance,
C_b[F]: Communication line (TxDq) load capacitance, V_b[V]: Communication line voltage

2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)

3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).
m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

4. UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (1/3)

(T_A = –40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{KCY1} \geq 4/f_{CLK}$	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ	600		ns
			2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	1000		ns
			2.4 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ	2300		ns
SCKp high-level width	t_{KH1}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		$t_{KCY1}/2 - 150$		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		$t_{KCY1}/2 - 340$		ns
		2.4 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ		$t_{KCY1}/2 - 916$		ns
SCKp low-level width	t_{KL1}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		$t_{KCY1}/2 - 24$		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		$t_{KCY1}/2 - 36$		ns
		2.4 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ		$t_{KCY1}/2 - 100$		ns

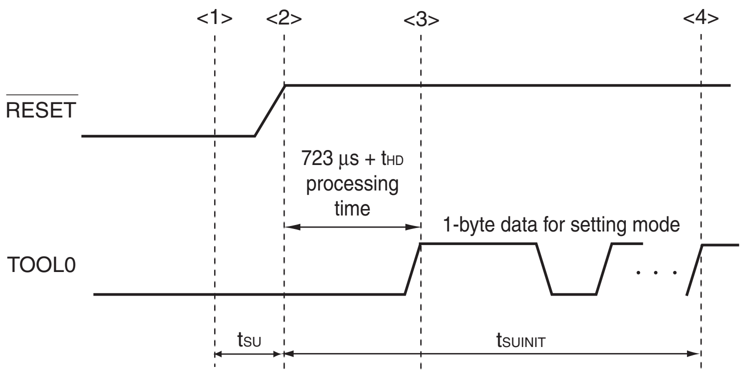
Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(**Remarks** are listed two pages after the next page.)

3.10 Timing of Entry to Flash Memory Programming Modes

(T_A = –40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	t_{SUINIT}	POR and LVD reset must be released before the external reset is released.			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	t_{SU}	POR and LVD reset must be released before the external reset is released.	10			µs
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)	t_{HD}	POR and LVD reset must be released before the external reset is released.	1			ms



<1> The low level is input to the TOOL0 pin.

<2> The external reset is released (POR and LVD reset must be released before the external reset is released.).

<3> The TOOL0 pin is set to the high level.

<4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

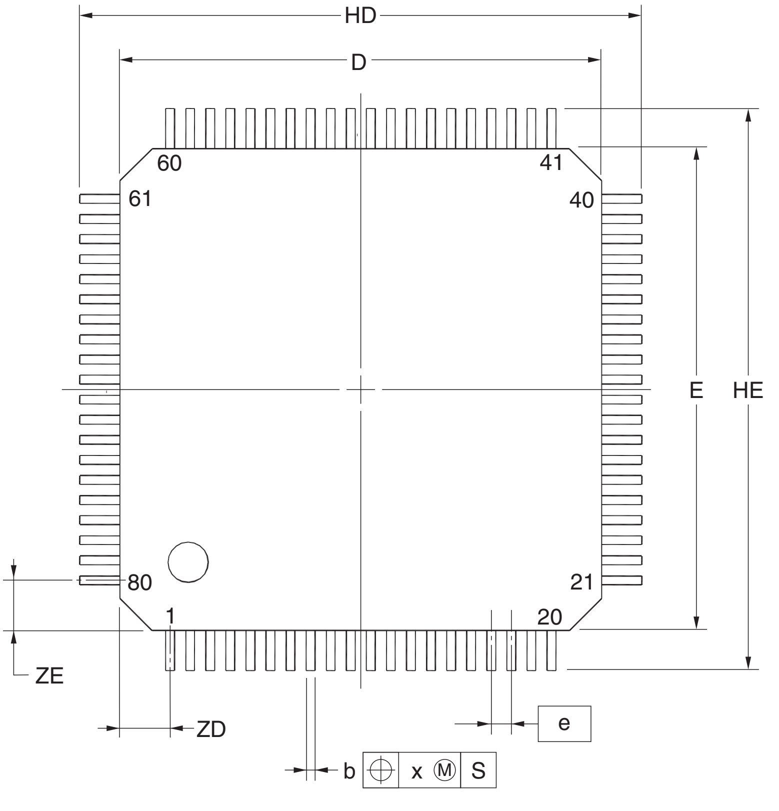
Remark t_{SUINIT}: Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.

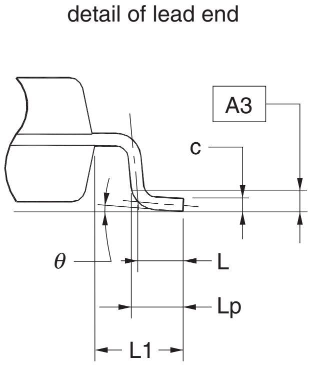
t_{SU}: Time to release the external reset after the TOOL0 pin is set to the low level

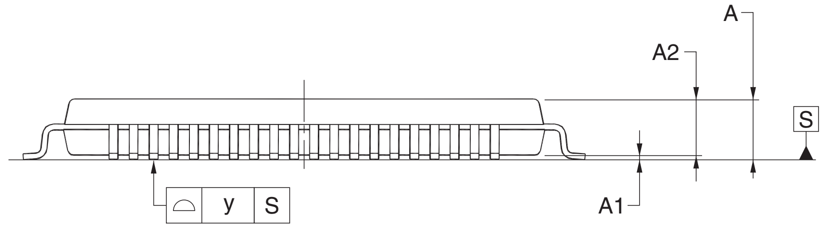
t_{HD}: Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)

R5F100MFAFB, R5F100MGAFB, R5F100MHAFB, R5F100MJAFB, R5F100MKAFB, R5F100MLAFB
R5F101MFAFB, R5F101MGAFB, R5F101MHAFB, R5F101MJAFB, R5F101MKAFB, R5F101MLAFB
R5F100MFDFB, R5F100MGDFB, R5F100MHDFB, R5F100MJDFB, R5F100MKDFB, R5F100MLDFB
R5F101MFDFB, R5F101MGDFB, R5F101MHDFB, R5F101MJDFB, R5F101MKDFB, R5F101MLDFB
R5F100MFGFB, R5F100MGGFB, R5F100MHGFB, R5F100MJGFB

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP80-12x12-0.50	PLQP0080KE-A	P80GK-50-8EU-2	0.53







(UNIT:mm)

ITEM	DIMENSIONS
D	12.00±0.20
E	12.00±0.20
HD	14.00±0.20
HE	14.00±0.20
A	1.60 MAX.
A1	0.10±0.05
A2	1.40±0.05
$\boxed{\text{A3}}$	0.25
b	0.22±0.05
c	$0.145^{+0.055}_{-0.045}$
L	0.50
Lp	0.60±0.15
L1	1.00±0.20
θ	$3^{\circ}{}^{+5^{\circ}}_{-3^{\circ}}$
$\boxed{\text{e}}$	0.50
x	0.08
y	0.08
ZD	1.25
ZE	1.25

NOTE
Each lead centerline is located within 0.08 mm of its true position at maximum material condition.